SILICON NPN TRIPLE DIFFUSED MESA TYPE

BUY71

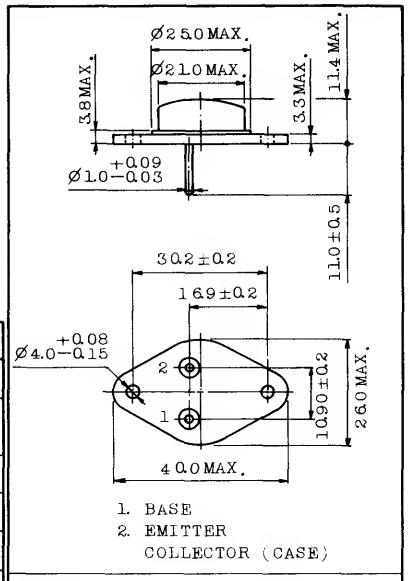
TV HORIZONTAL OUTPUT APPLICATION.

FEATURES:

. High Voltage : V_{CEX}=2200V

. Fast Switching : t_f=0.7μs (Typ.)

Unit in mm



JEDEC	TO-3
EIAJ	TC-3, TB-3
TOSHIBA	2-21B1A

Weight : 17.0g

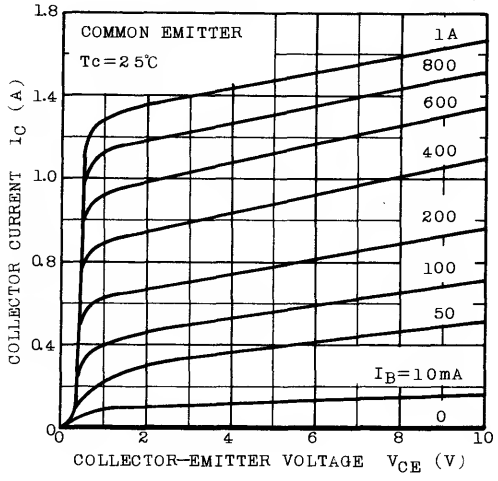
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	2200	V
Peak Collector-Emitter Voltage	V_{CEX}	2200	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Base Current	I_B	2	A
Collector Power Dissipation (Tc≦80°C)	P_C	10	W
Junction Temperature	T_j	100	°C
Storage Temperature Range	T_{stg}	-60 ~ 100	°C

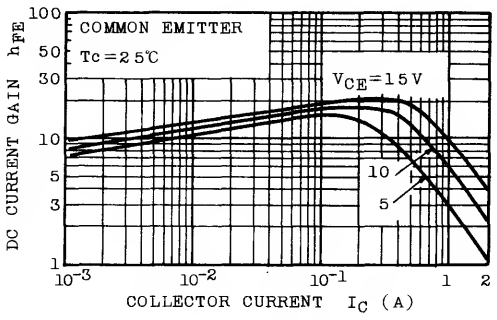
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Cut-off Current	I_{CEX}	V_{CE}=2200V, V_{BE}=-2V	-	-	1	mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=100mA, I_C=0	5	-	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1.5A, I_B=1.5A	-	-	10	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=1.5A, I_B=1.5A	-	-	1.5	V
Transition Frequency	f_T	V_{CE}=5V, I_C=0.1A	-	4	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz	-	50	-	pF
Fall Time	t_f	I_{cp}=1.2A $I_{B1(end)}$=0.55A	-	0.7	-	μs

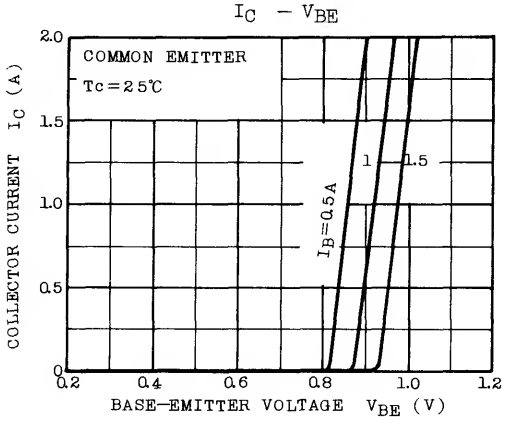
I_C – V_{CE} (LOW VOLTAGE REGION)

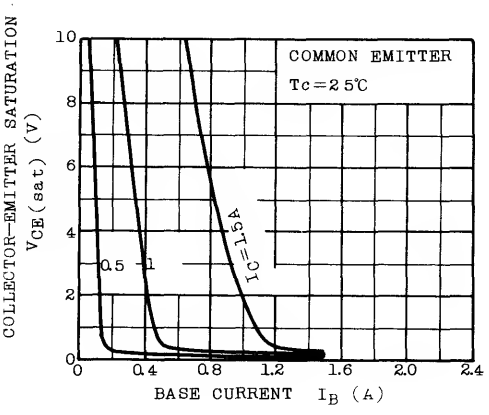


h_{FE} – I_C



I_C – V_{BE}





P_C – Tc